

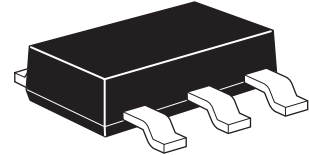
# ZXMN7A11G

## 70V N-channel enhancement mode MOSFET

### Summary

$V_{DSS}=70V$  :  $R_{DS(on)}=0.13\Omega$

$I_D=3.8A$

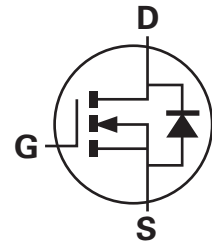


### Description

This new generation of trench MOSFETs from Zetex utilizes a unique structure that combines the benefits of low on-resistance with fast switching speed. This makes them ideal for high efficiency, low voltage power management applications.

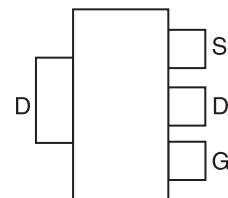
### Features

- Low on-resistance
- Fast switching speed
- Low threshold
- Low gate drive
- SOT223 package



### Applications

- DC-DC converters
- Power management functions
- Disconnect switches
- Motor control
- Class D audio output stages



### Ordering information

Device	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXMN7A11GTA	7	12	1,000
ZXMN7A11GTC	13	12	4,000

### Device marking

ZXMN  
7A11

# ZXMN7A11G

## Absolute maximum ratings

Parameter	Symbol	Limit	Unit
Drain-source voltage	$V_{DSS}$	70	V
Gate-source voltage	$V_{GS}$	$\pm 20$	V
Continuous drain current @ $V_{GS}=10V$ ; $T_A=25^\circ C^{(b)}$	$I_D$	3.8	A
@ $V_{GS}=10V$ ; $T_A=70^\circ C^{(b)}$		3.0	A
@ $V_{GS}=10V$ ; $T_A=25^\circ C^{(a)}$		2.7	A
Pulsed drain current <sup>(c)</sup>	$I_{DM}$	10	A
Continuous source current (body diode) <sup>(b)</sup>	$I_S$	5	A
Pulsed source current (body diode) <sup>(c)</sup>	$I_{SM}$	10	A
Power dissipation at $T_A = 25^\circ C^{(a)}$	$P_D$	2	W
Linear derating factor		16	mW/ $^\circ C$
Power dissipation at $T_A = 25^\circ C^{(b)}$	$P_D$	3.9	W
Linear derating factor		31	mW/ $^\circ C$
Operating and storage temperature range	$T_j, T_{stg}$	-55 to +150	$^\circ C$

## Thermal resistance

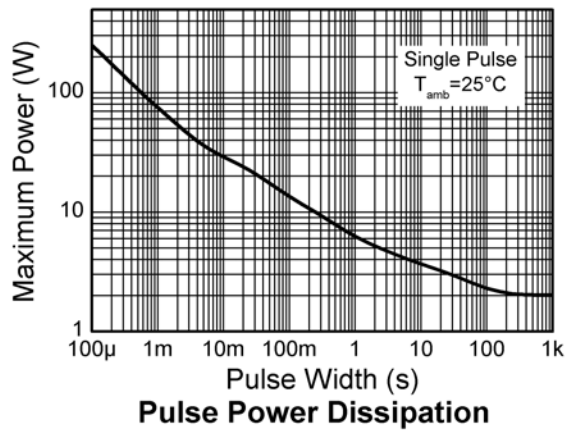
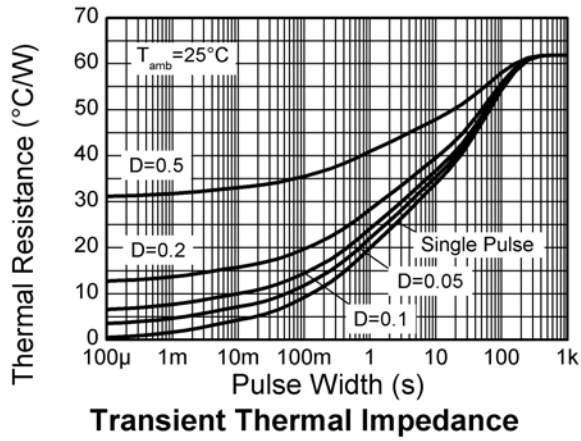
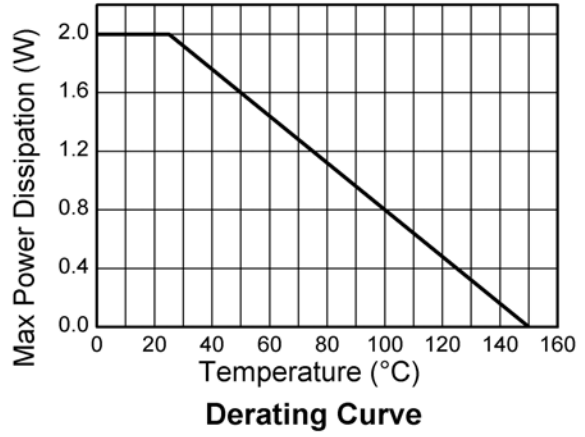
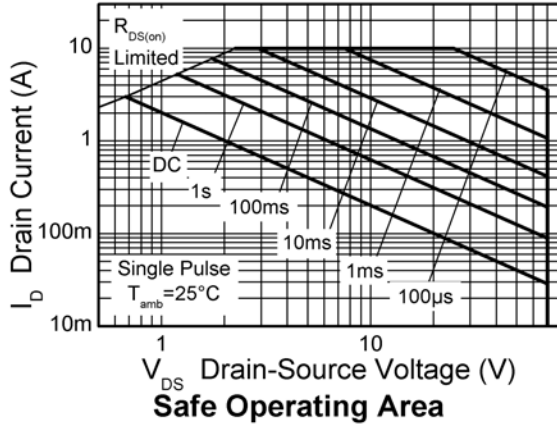
Parameter	Symbol	Limit	Unit
Junction to ambient <sup>(a)</sup>	$R_{\theta JA}$	62.5	$^\circ C/W$
Junction to ambient <sup>(b)</sup>	$R_{\theta JA}$	32	$^\circ C/W$

### NOTES:

- (a) For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.
- (b) For a device surface mounted on FR4 PCB measured at  $t \leq 5$  sec.
- (c) Repetitive rating 25mm x 25mm FR4 PCB,  $D=0.05$  pulse width=10 $\mu s$  - pulse width limited by maximum junction temperature.

# ZXMN7A11G

## Characteristics



# ZXMN7A11G

## Electrical characteristics (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
<b>Static</b>						
Drain-source breakdown voltage	$V_{(BR)DSS}$	70			V	$I_D = 250\mu\text{A}$ , $V_{GS} = 0\text{V}$
Zero gate voltage drain current	$I_{DSS}$			1	$\mu\text{A}$	$V_{DS} = 70\text{V}$ , $V_{GS} = 0\text{V}$
Gate-body leakage	$I_{GSS}$			100	nA	$V_{GS} = \pm 20\text{V}$ , $V_{DS} = 0\text{V}$
Gate-source threshold voltage	$V_{GS(th)}$	1.0			V	$I_D = 250\mu\text{A}$ , $V_{DS} = V_{GS}$
Static drain-source on-state resistance <sup>(*)</sup>	$R_{DS(on)}$			0.13	$\Omega$	$V_{GS} = 10\text{V}$ , $I_D = 4.4\text{A}$
				0.19	$\Omega$	$V_{GS} = 4.5\text{V}$ , $I_D = 3.8\text{A}$
Forward transconductance <sup>(*)(‡)</sup>	$g_{fs}$		4.66		S	$V_{DS} = 15\text{V}$ , $I_D = 4.4\text{A}$
<b>Dynamic<sup>(‡)</sup></b>						
Input capacitance	$C_{iss}$		298		pF	$V_{DS} = 40\text{V}$ , $V_{GS} = 0\text{V}$ $f = 1\text{MHz}$
Output capacitance	$C_{oss}$		35		pF	
Reverse transfer capacitance	$C_{rss}$		21		pF	
<b>Switching<sup>(†)(‡)</sup></b>						
Turn-on-delay time	$t_{d(on)}$		1.9		ns	$V_{DD} = 35\text{V}$ , $I_D = 1\text{A}$ $R_G = 6.0\Omega$ , $V_{GS} = 10\text{V}$
Rise time	$t_r$		2		ns	
Turn-off delay time	$t_{d(off)}$		11.5		ns	
Fall time	$t_f$		5.8		ns	
Total gate charge	$Q_g$		4.35		nC	$V_{DS} = 35\text{V}$ , $V_{GS} = 5\text{V}$ $I_D = 4.4\text{A}$
Total gate charge	$Q_g$		7.4		nC	$V_{DS} = 35\text{V}$ , $V_{GS} = 10\text{V}$ $I_D = 4.4\text{A}$
Gate-source charge	$Q_{gs}$		1.06		nC	
Gate drain charge	$Q_{gd}$		1.8		nC	
<b>Source-drain diode</b>						
Diode forward voltage <sup>(*)</sup>	$V_{SD}$		0.85	0.95	V	$T_j = 25^{\circ}\text{C}$ , $I_S = 2.5\text{A}$ , $V_{GS} = 0\text{V}$
Reverse recovery time <sup>(‡)</sup>	$t_{rr}$		19.8		ns	$T_j = 25^{\circ}\text{C}$ , $I_S = 2.5\text{A}$ , $di/dt = 100\text{A}/\mu\text{s}$
Reverse recovery charge <sup>(‡)</sup>	$Q_{rr}$		14		nC	

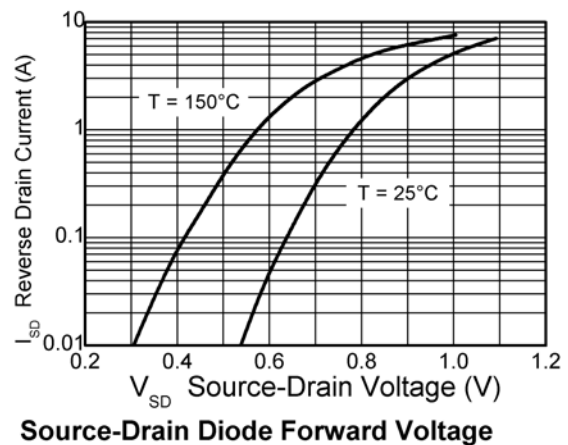
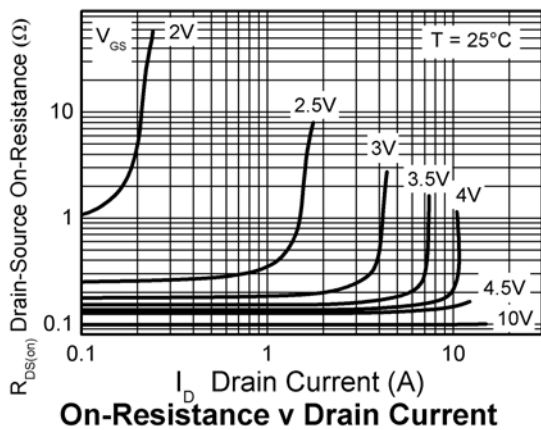
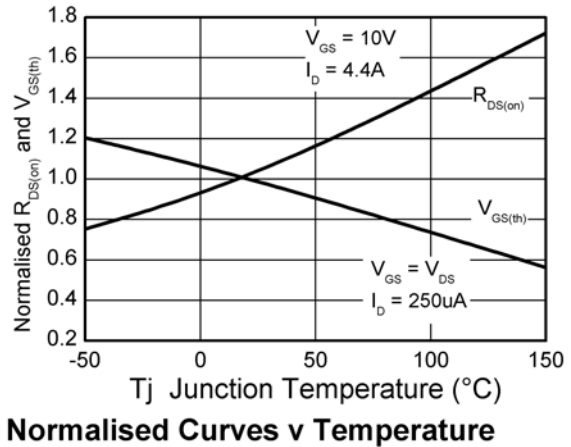
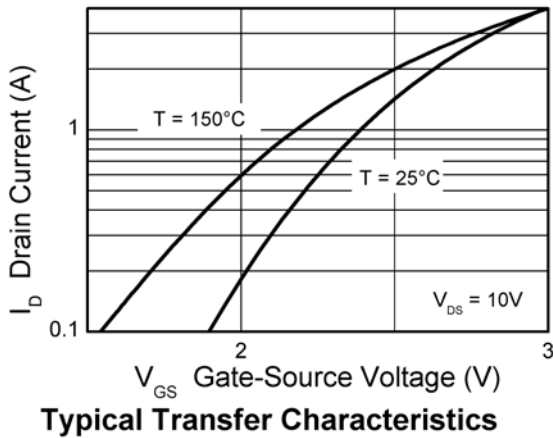
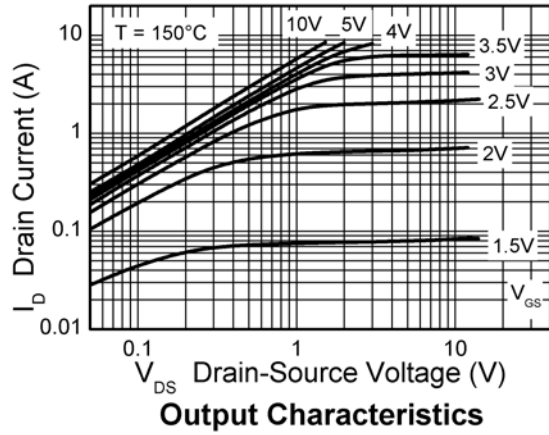
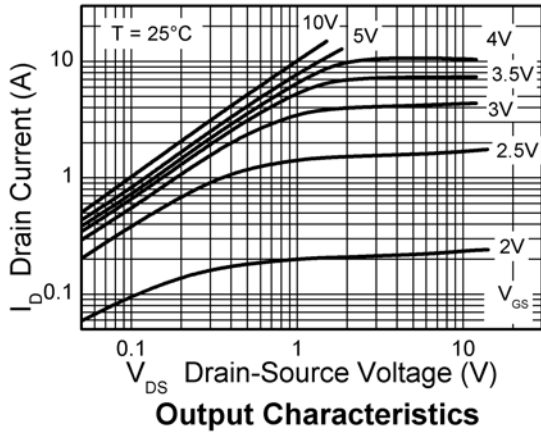
### NOTES:

(\*) Measured under pulsed conditions. Pulse width  $\leq 300\mu\text{s}$ ; duty cycle  $\leq 2\%$ .

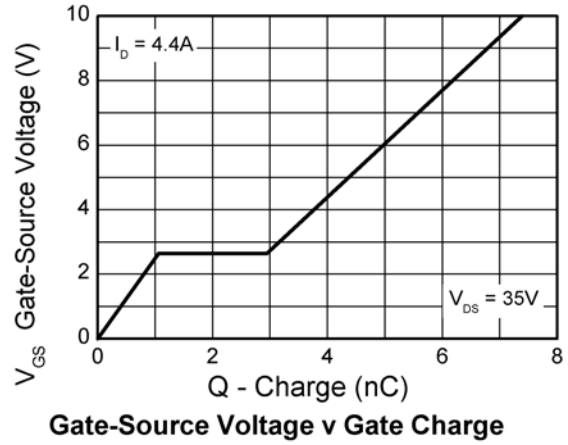
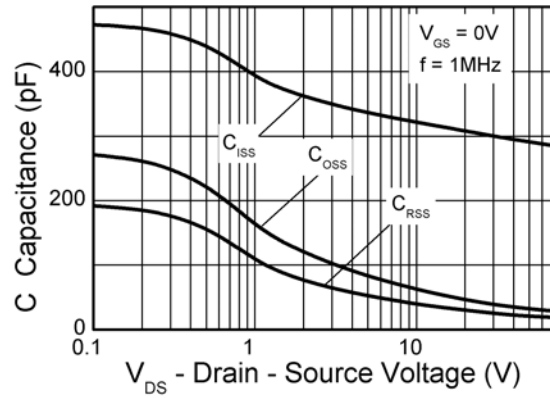
(†) Switching characteristics are independent of operating junction temperature.

(‡) For design aid only, not subject to production testing.

## Typical characteristics



## Typical characteristics

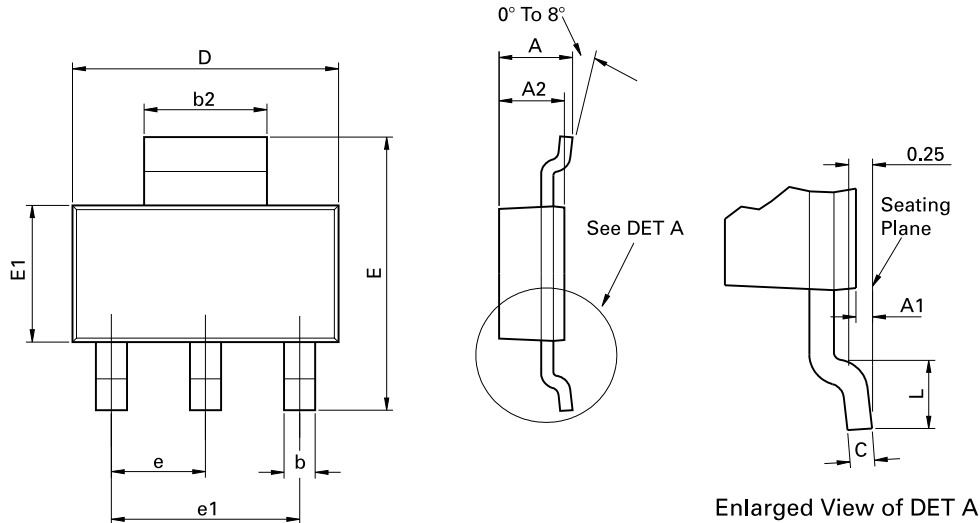


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## Package outline - SOT223



Conforms to JEDEC TO-261 AA Issue B

DIM	Millimeters		Inches		DIM	Millimeters		Inches	
	Min	Max	Min	Max		Min	Max	Min	Max
A	-	1.80	-	0.071	e	2.30 BSC		0.0905 BSC	
A1	0.02	0.10	0.0008	0.004	e1	4.60 BSC		0.181 BSC	
b	0.66	0.84	0.026	0.033	E	6.70	7.30	0.264	0.287
b2	2.90	3.10	0.114	0.122	E1	3.30	3.70	0.130	0.146
C	0.23	0.33	0.009	0.013	L	0.90	-	0.355	-
D	6.30	6.70	0.248	0.264	-	-	-	-	-

**Note:** Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

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